

YJ Planar Schottky Barrier Diode Die Specification

40V 0.5A, 25mil, Schottky barrier diode die based on silicon planar process

Part No.: PSB025L040AS-180A

Main Products Characteristics

- Average forward current: $I_F(AV) = 0.5 \text{ A}$
- Maximum operating junction temperature: $T_j = 125 \text{ }^\circ\text{C}$
- Top metal: AL

Maximum Ratings

Static Electrical Characteristics ($T_a = 25^\circ\text{C}$)

$I_F = 0.5 \text{ A}$

Pulse Test: $t_p = 300 \mu\text{s}$, 2%

Device Schematics and Outline Drawing

Die Thickness *

Die Size **

Top Metal Pad

Active Area

Top Metal

Back Metal

Note: 1 * : Also can offer device with 10.5 mils thickness

2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

does not guarantee device performance after assembly.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.